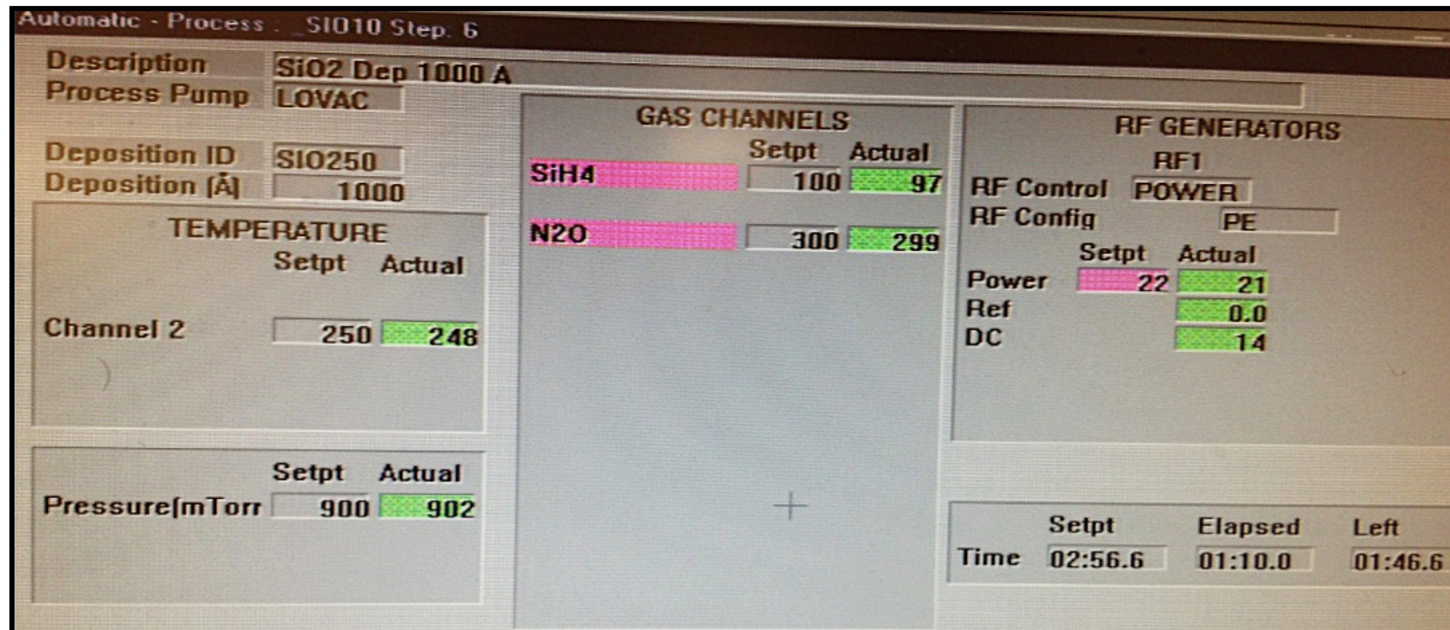
PECVD-SIO2 standard recipe-1000A			PECVD1 SIO2 1000A Typical Film Properties
1. Chamber Clean (wet clean)	**2. Chamber (clean+coat)**	**3.SIO2 Deposition**	**Deposition rate=11.21nm/min**
WET CLEAN	**30CLN_SO**	**SiO_10**	**Refractive index@632.8nm=1.938**
Wipe clean upper chamber walls with DI	step1: Initial t=10", p=2x10-2 T=250C	step1: Initial t=10"	**Stress=508.86MPa**
Wipe off upper chamber walls with IPA	step2: N2 purge t=30" p=300mT	step2: N2 purge t=30"	**HF etch rate=85.52nm/min**
	step3: evacuate, base pressure=2x10-2, t=10"	step3: evacuate, t=10"	
	step4:loop	step4:loop	
	step5:gass stabilization, t=30"	step5: SiO2 gass stabilization, t=30"	
	step6:etch chamber, t=30'	**step6:SiO2 deposition**	
	step7:evacuate, t=10"	**Time=2'56.6"**	
	step8:N2 purge	**Temperature=250°C**	
	step9:evacuate	**Pressure=900mT**	
	step10:loop	**Gass Flow:**	
	step11:SiO2 gass stabilization	**SiH4=100sccm**	
	step12:SiO2 deposition(200A coat)	**N2O= 300sccm**	
	step13:evacuate	**Power:**	
	step14:N2purge, t=30"	**RF1=22W**	
	step15:end	step7:evacuate, t=10"	
		step8:N2 purge t=30"	
		step9:evacuate t=10"	
		step10:loop	



	Setpt	Actual
Pressure(mTorr	900	902

	Setpt	Elapsed	Left
Time	02:56.6	01:10.0	01:46.6

Left
01:46.6

Left
01:46.6